

ESDU5V6P

SILICON EPITAXIAL PLANAR DIODE

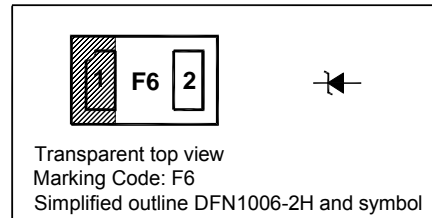
ESD protection diode

Features

- Ultra small mold type
- high reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

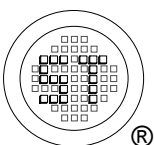
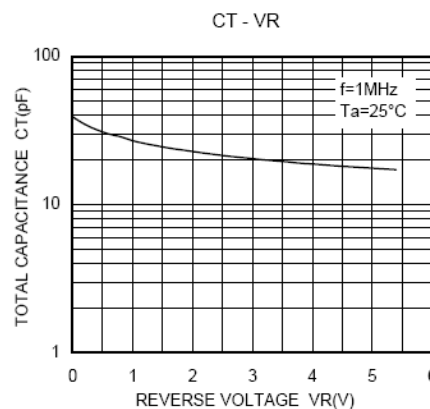
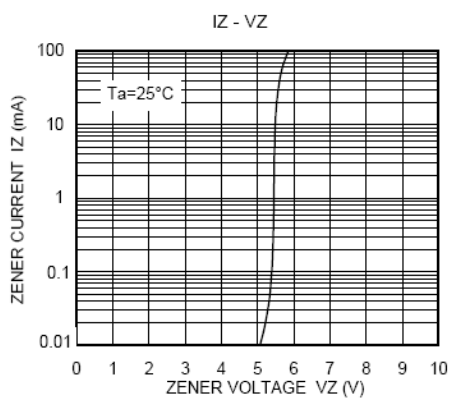


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
IEC61000-4-2 (ESD) Contact	V_{ESD}	± 15	KV
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$
Operation Temperature Range	T_{opr}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Zener Voltage at $I_Z = 5 \text{ mA}$	V_Z	5.3	-	6	V
Reverse Current at $V_R = 3.5 \text{ V}$	I_R	-	-	1	μA
Dynamic Impedance at $I_{ZT} = 5 \text{ mA}$	Z_{ZT}	-	-	30	Ω
Capacitance between Terminals at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_T	-	40	-	pF



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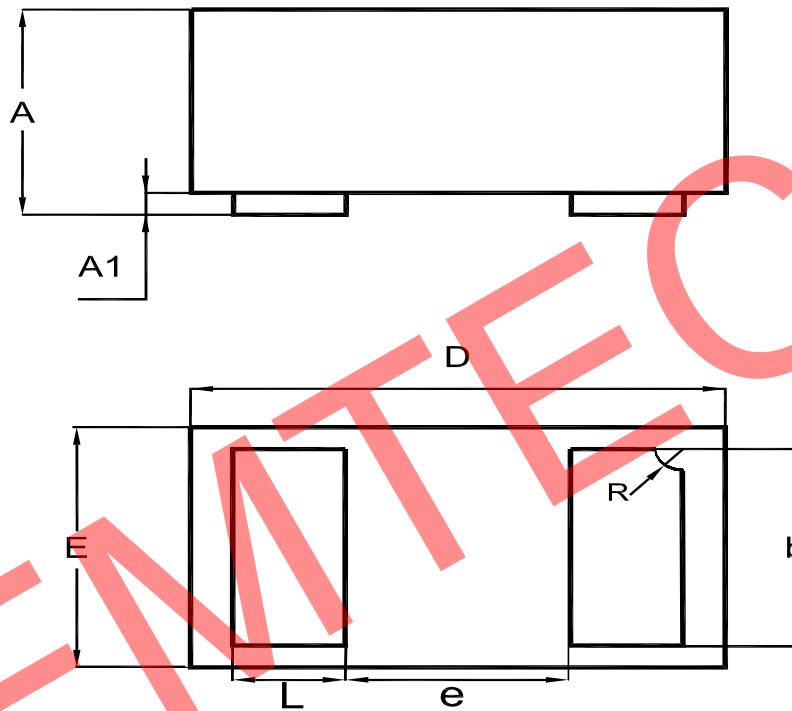


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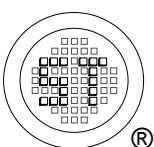
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51	0.05	0.55	1.075	0.675	0.4	0.3	0.15
	0.46	0	0.45	0.95	0.55		0.2	0.05



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Dated: 01/07/2013 Rev: 01